



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业微信二维码



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## Product Summary

$V_{(BR)DSS}$	$R_{DS(on) Max}$	$I_D Max$ $T_A = +25^\circ C$ (Note 7)
-60V	125mΩ @ $V_{GS} = -10V$	-3.0 A
	190mΩ @ $V_{GS} = -4.5V$	-2.4 A

## Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Input Capacitance

## Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

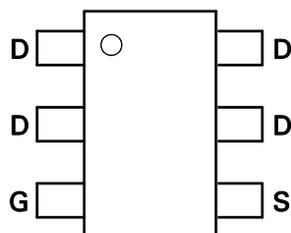
- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

## Mechanical Data

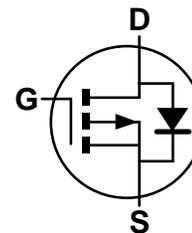
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 <sup>Ⓔ</sup>
- Weight: 0.018 grams (Approximate)



Top View



Pin Out - Top View



Equivalent Circuit

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

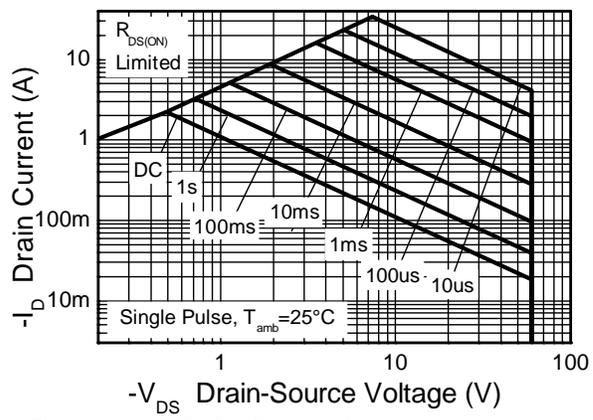
Characteristic			Symbol	Value	Unit	
Drain-Source Voltage			$V_{DSS}$	-60	V	
Gate-Source Voltage			$V_{GS}$	$\pm 20$	V	
Continuous Drain Current	$V_{GS} = 10\text{V}$	(Note 7)	$I_D$	-3.0	A	
		$T_A = +70^\circ\text{C}$ (Note 7)		-2.4		
		(Note 6)		-2.3		
Pulsed Drain Current	$V_{GS} = 10\text{V}$	(Note 8)	$I_{DM}$	-13.6	A	
Continuous Source Current (Body Diode)			(Note 7)	$I_S$	-2.5	A
Pulsed Source Current (Body Diode)			(Note 8)	$I_{SM}$	-13.6	A

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

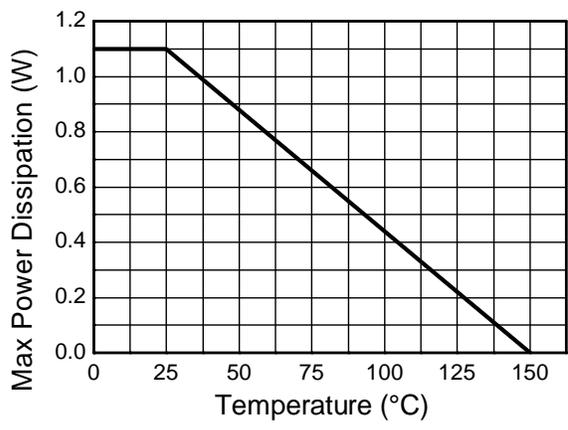
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	$P_D$	1.1	W
	Linear Derating factor		8.8	
(Note 7)			1.92	
			15.4	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	113	$^\circ\text{C/W}$
	(Note 7)		65	
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

- Notes:
6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  7. Same as Note 6, except the device is measured at  $t \leq 5$  sec.
  8. Same as Note 6, except the device is pulsed with  $D = 0.02$  and pulse width 300 $\mu\text{s}$ . The pulse current is limited by the maximum junction temperature.

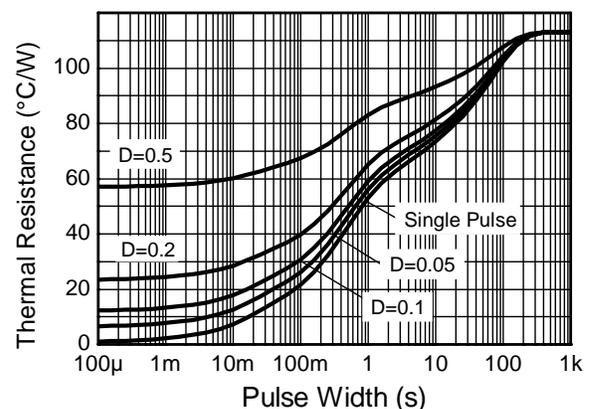
### Thermal Characteristics



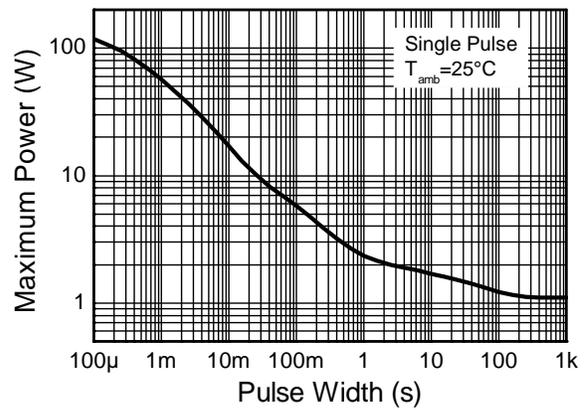
**P-channel Safe Operating Area**



**Derating Curve**



**Transient Thermal Impedance**



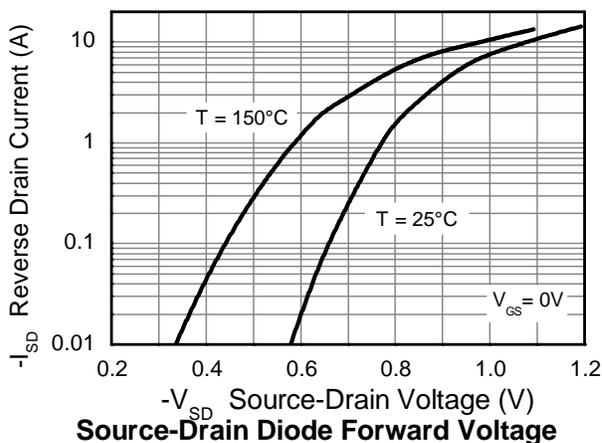
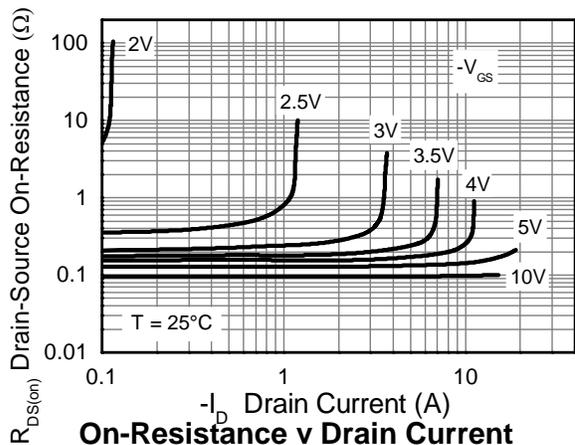
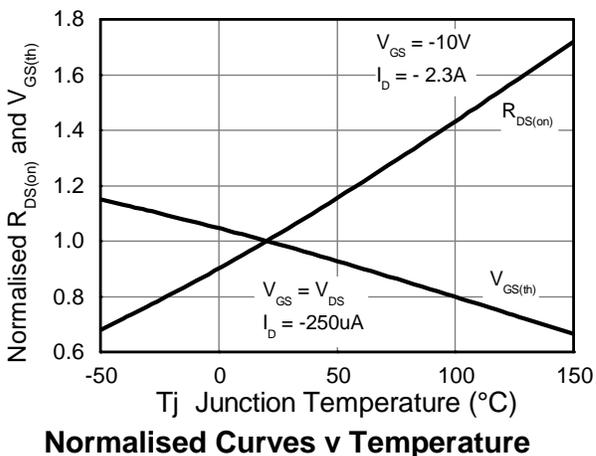
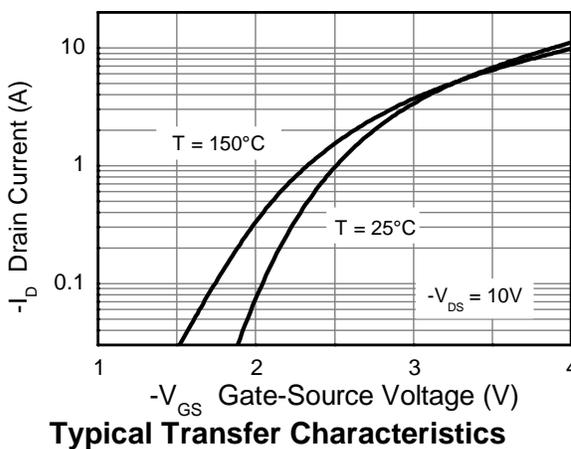
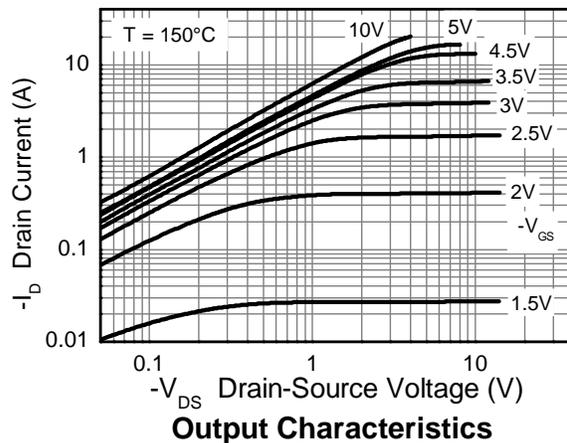
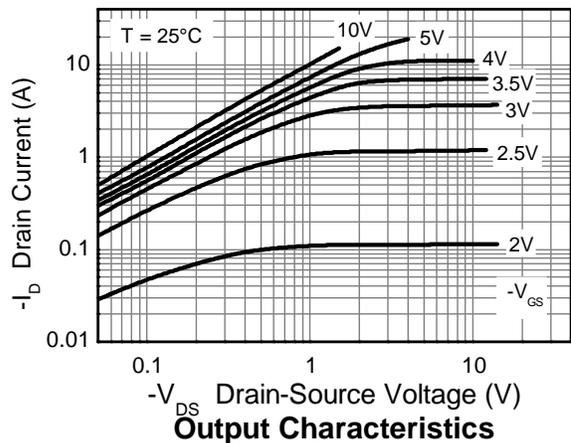
**Pulse Power Dissipation**

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

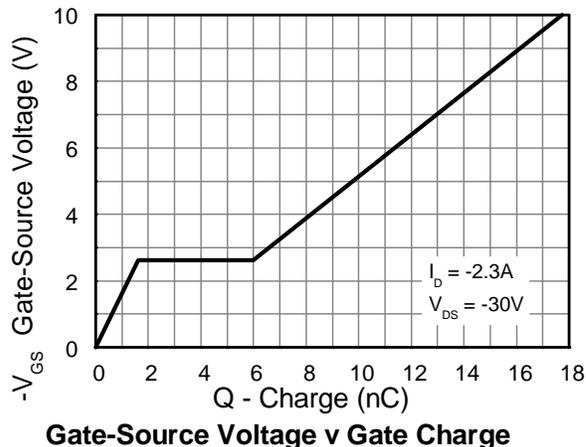
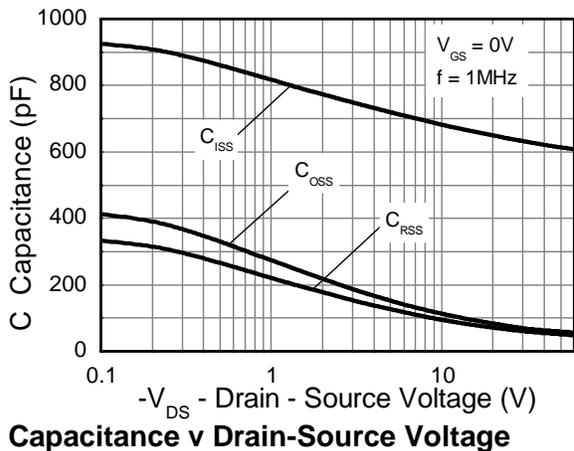
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	—	—	V	I <sub>D</sub> = -250μA, V <sub>GS</sub> = 0V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1.0	μA	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	—	-3.0	V	I <sub>D</sub> = -250μA, V <sub>DS</sub> = V <sub>GS</sub>
Static Drain-Source On-Resistance (Note 9)	R <sub>DS(on)</sub>	—	0.100	0.125	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -2.3A
			0.130	0.190		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.9A
Forward Transconductance (Notes 9 & 10)	g <sub>fs</sub>	—	4.7	—	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -2.3A
Diode Forward Voltage (Note 9)	V <sub>SD</sub>	—	-0.85	-0.95	V	I <sub>S</sub> = -2.0A, V <sub>GS</sub> = 0V
Reverse Recovery Time (Note 10)	t <sub>rr</sub>	—	25.1	—	ns	I <sub>F</sub> = -1.7A, di/dt = 100A/μs
Reverse Recovery Charge (Note 10)	Q <sub>rr</sub>	—	27.2	—	nC	
<b>DYNAMIC CHARACTERISTICS (Note 10)</b>						
Input Capacitance	C <sub>iss</sub>	—	637	—	pF	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	70	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	53	—	pF	
Total Gate Charge (Note 11)	Q <sub>g</sub>	—	9.8	—	nC	V <sub>GS</sub> = -5.0V
Total Gate Charge (Note 11)	Q <sub>g</sub>	—	17.7	—	nC	V <sub>GS</sub> = -10V V <sub>DS</sub> = -30V I <sub>D</sub> = -2.3A
Gate-Source Charge (Note 11)	Q <sub>gs</sub>	—	1.6	—	nC	
Gate-Drain Charge (Note 11)	Q <sub>gd</sub>	—	4.4	—	nC	
Turn-On Delay Time (Note 11)	t <sub>D(on)</sub>	—	2.6	—	ns	V <sub>DD</sub> = -30V, V <sub>GS</sub> = -10V I <sub>D</sub> = -1.0A, R <sub>G</sub> ≅ 6.0Ω
Turn-On Rise Time (Note 11)	t <sub>r</sub>	—	3.4	—	ns	
Turn-Off Delay Time (Note 11)	t <sub>D(off)</sub>	—	26.2	—	ns	
Turn-Off Fall Time (Note 11)	t <sub>f</sub>	—	11.3	—	ns	

- Notes:
9. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%.
  10. For design aid only, not subject to production testing.
  11. Switching characteristics are independent of operating junction temperatures.

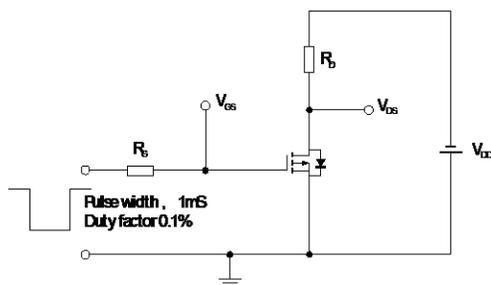
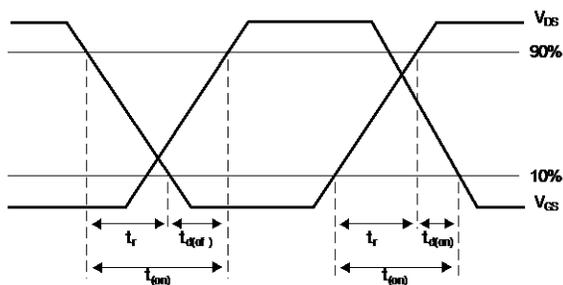
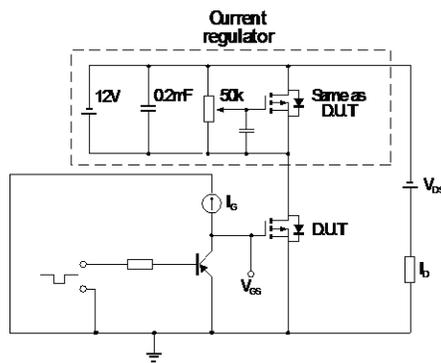
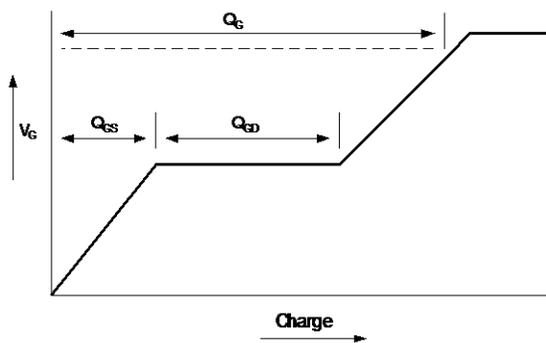
Typical Characteristics



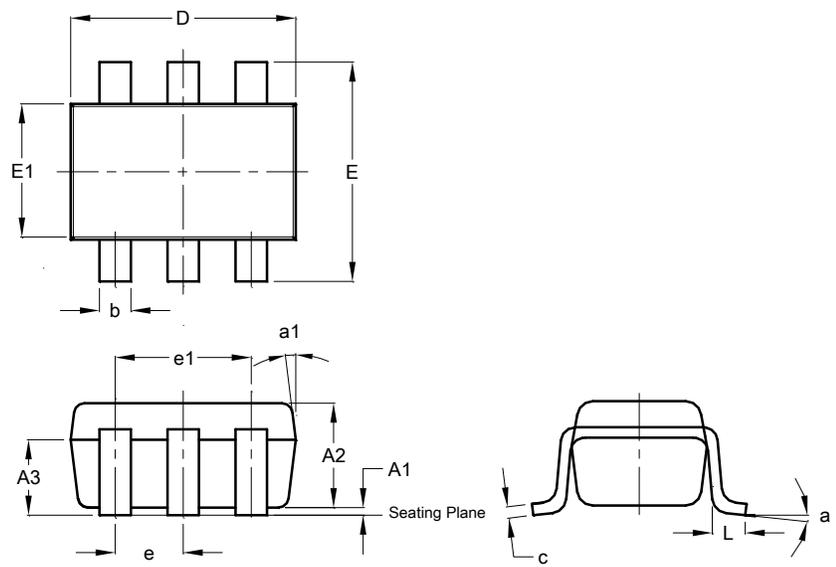
**Typical Characteristics** (cont.)



**Test Circuits**

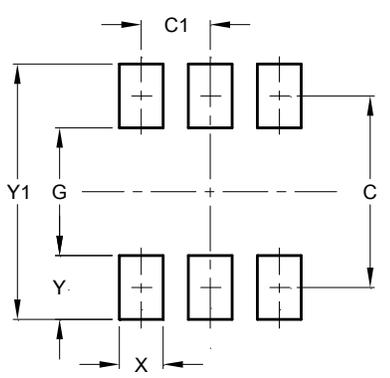


**Package Outline Dimensions**



SOT26			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20